

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	181	361/10	US-PGPUB; USPAT	OR	OFF	2006/03/21 09:26
S2	243	"1" and (pad adj cell)	US-PGPUB; USPAT	OR	OFF	2006/02/07 08:50
S3	181	361/10	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:02
S4	0	S3 and (pad adj cell)	US-PGPUB; USPAT	OR	OFF	2006/02/07 08:50
S5	20456	pin same pad	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:02
S6	2124	S5 same (IC (integrated adj circuit))	US-PGPUB; USPAT	OR	OFF	2006/02/07 14:21
S7	628	S6 same signal	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:03
S8	105	S7 same path	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:32
S9	0	(pad adj cell) same (signal adj path)	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:34
S10	119	pad same (signal adj path) same (pin pins)	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:34
S11	81	S10 not S8	US-PGPUB; USPAT	OR	OFF	2006/02/07 09:35
S12	3	("4346309" "5514976" "6292342").PN. OR ("6900628").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 11:34
S13	12993	(pin pins) same (chip chips) same (ic (integrated adj circuit) (internal adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:41
S14	3786	S13 same (signal (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 11:39
S15	140	S13 same (signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 11:39
S16	20	S15 same (operate operating operation)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 11:39
S17	3	((("5602409") or ("5751525") or ("6236087")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 14:22

EAST Search History

S18	4091	(pin pins) same (chip chips) same (pad)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:53
S19	1	(pin pins) same (chip chips) same (cell adj pad)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:47
S20	28	S18 same (signal adj path)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:47
S21	1592	S18 same (IC integrated internal)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:54
S22	451	S21 same signal	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 16:03
S23	75	S22 same protect\$5	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2006/02/07 14:55
S24	5	("4296456" "5731945" "5807791" "6141245").PN. OR ("6329863").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/02/07 15:53
S25	181	361/10	US-PGPUB; USPAT	OR	OFF	2006/02/08 08:02
S26	28	"5602409" "5751525" "6236087"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 09:56
S27	5586	pin same pad same (ic integrated)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 09:57
S28	1322	S27 same (signal path\$1)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 10:44

EAST Search History

S29	35	S28 same (operable non\$1operable)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 09:58
S30	1466703	ic (integrated adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 11:26
S31	131	S30 same (external near pin) same (pad (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 11:42
S32	0	S30 same (external near pin) same (pad adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 11:43
S33	12	S30 same (pin) same (pad adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 11:47
S34	1	("6900628").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/21 11:47
S35	3	("4346309" "5514976" "6292342").PN. OR ("6900628").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/21 11:47
S36	5	("4296456" "5731945" "5807791" "6141245").PN. OR ("6329863").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/21 14:14
S37	194	(external near pin) same (pad) same (ic integrated internal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 14:45

EAST Search History

S38	13	S37 same signal same path	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 14:17
S39	2	(pad adj cell) same (signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 14:46
S40	0	(pad adj cell) same (second adj signal adj path)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 14:46
S41	39	(pad) same (second adj signal adj path)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:26
S42	1478931	ic (integrated adj circuit) (internal adj circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:28
S43	390	S42 same (pin (external adj pin) (external near pin)) same (signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:30
S44	12	S42 same (pin (external adj pin) (external near pin)) same (second adj signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:40
S45	260294	S42 and (pin (external adj pin) (external near pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:41

EAST Search History

S46	5353	S45 and (signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:41
S47	193	S45 and (second adj signal adj (path paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:48
S48	29	multiple same (pad adj (cell cells))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/21 15:48
S49	7626	(signal adj path) same (operable operating operate operates)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:41
S50	172	S49 same (pin (external near pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:28
S51	104	S49 same (pad (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:28
S52	6	S50 same (pad (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:28
S53	13	S49 same (non\$1operable non\$1operating)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:46

EAST Search History

S54	2	(pad adj cell) same (signal adj paths)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 07:57
S55	344	(pad) same (signal adj paths)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 08:08
S56	27	S55 same pin	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 09:33
S57	2289	second adj signal adj path	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 16:06
S58	46	S57 same (pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 11:35
S59	1328	second adj signal adj path	USPAT	OR	OFF	2006/03/22 11:52
S60	23	S59 same (pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 11:35
S61	123	S59 and (pad pads (pad adj cell))	USPAT	OR	OFF	2006/03/22 11:52
S62	8	("5691570" "5889327" "5898636" "6163459" "6307769" "6370054").PN. OR ("6667895"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/22 13:37
S63	38	"5903512" "6667895" "5757680" "6643324"	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/22 13:42
S64	4	((("5903512") or ("6667895") or ("6643324") or ("5757680"))).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/22 14:17

EAST Search History

S65	1678	(second adj signal adj path) same (first adj signal adj path)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 14:18
S66	40	S65 same (pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 16:06
S67	0	S66 same (pin (external near pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 14:18
S68	140	S57 same (transistor MOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/22 16:06
S69	140	(second adj signal adj path) same (mos transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:58
S70	18	S69 and (pin (external near pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:42
S71	346	pad adj cell	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:59
S72	2	S71 same (signal adj paths)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:59

EAST Search History

S73	697667	pad pads (pad adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:59
S74	786	S73 same (signal adj paths)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 07:59
S75	8	S73 same (multiple adj signal adj paths)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:46
S76	1585347	(pin (external near pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:50
S77	125892	S76 and (pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:50
S78	1769	S77 and ((multiple adj signal adj paths) (signal adj paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:50
S79	646224	(pin (external near pin))	US-PGPUB; USPAT	OR	OFF	2006/03/23 08:50
S80	87491	S79 and (pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:50
S81	1756	S80 and ((multiple adj signal adj paths) (signal adj paths))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:51

EAST Search History

S82	1234	S81 and (operating operates operable)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:51
S83	1545	S81 and (operating operates operable operation)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:51
S84	3	S83 and ((non adj operable) (non adj operating))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/23 08:52
S85	250	pad adj cell	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:08
S86	0	S85 and (multiple adj signal adj paths)	US-PGPUB; USPAT	OR	OFF	2006/03/23 08:59
S87	5	S85 and (signal adj paths)	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:07
S88	5	S85 and (signal near paths)	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:07
S89	387070	(pad adj cell) pad pads	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:09
S90	3662	S89 and (signal adj paths)	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:09
S91	728	S89 same (signal adj paths)	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:38
S92	2465	307/116	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:38
S93	477	S92 and (pin (external near pin))	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:38
S94	85	S93 and (pad pads (pad adj cell))	US-PGPUB; USPAT	OR	OFF	2006/03/23 09:42
S95	14853	esd (electrostatic adj discharge)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:19
S96	7708	S95 same (protect protection protecting protected)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:19
S97	2779	S96 same (MOS transistor)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:20
S98	516	S97 same (source same well)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:20

EAST Search History

S99	1839	second adj signal adj path	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:21
S10 0	92	S99 with (MOS transistor)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:31
S10 1	11837	(MOS transistor) with well with source	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:31
S10 2	547	S101 same (path (signal adj path))	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:32
S10 3	50	S102 same (protect protection protected protecting)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:41
S10 4	14853	(esd (electrostatic adj discharge))	US-PGPUB; USPAT	OR	OFF	2006/03/23 11:27
S10 5	1433	S104 same (pin (external near pin))	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:42
S10 6	444	S105 same (pad pads (pad adj cell))	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:42
S10 7	296	S106 same (ic ((integrated internal) adj (circuit)))	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:43
S10 8	276321	S107 same (path (signal adj (path paths))))]	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:44
S10 9	69	S107 same (path (signal adj (path paths)))	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:56
S11 0	11837	source with well with (transistor MOS)	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:56
S11 1	36	S110 with pin	US-PGPUB; USPAT	OR	OFF	2006/03/23 10:57
S11 2	38	S104 same (MOS transistor) same (comparator)	US-PGPUB; USPAT	OR	OFF	2006/03/23 11:27
S11 3	282	comparator same ((digital near gate) (analog adj amplifier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:08
S11 4	1260	source with well with (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:09
S11 5	360	S114 same (MOS NMOS transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:17

EAST Search History

S11 6	22	S115 and (comparator (digital adj gate) (analog adj amplifier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:22
S11 7	39924	(comparator adj (circuit circuitry))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:48
S11 8	4947	S117 same (MOS transistor NMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:23
S11 9	121	S118 same (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:23
S12 0	378738	(comparator adj (circuit circuitry) comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:48
S12 1	378738	(comparator adj (circuit circuitry) (comparator))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:48
S12 2	1553	S121 near (MOS transistor NMOS)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 09:49
S12 3	24	S122 same (pin (external adj pin) pad pads (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:13

EAST Search History

S12 4	31	("4567378" "4825099" "4906867" "5039874" "5140591" "5166558" "5237213" "5300830").PN. OR ("5598119"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/28 09:52
S12 5	2055724	(pad pin (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:13
S12 6	779	S125 same (comparator adj (circuit circuitry))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:16
S12 7	1	S126 same ((digital adj gate) (analog adj amplifier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:16
S12 8	0	S126 same ((analog adj amplifier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:16
S12 9	378738	(comparator adj (circuit circuitry)) comparator	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:17
S13 0	9	S129 same (analog adj amplifier) same (inverter)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:32
S13 1	130	S129 same (analog adj amplifier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:44

EAST Search History

S13 2	10	S129 near (analog adj amplifier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:35
S13 3	79	S129 with (analog adj amplifier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:54
S13 4	246651	"79" and (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:37
S13 5	13	S133 and (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 10:38
S13 6	2926	analog adj devices.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:06
S13 7	12354	comparator with (MOS transistor NMOS) with (series coupled connect\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:07
S13 8	10760	S137 same (input output)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:07
S13 9	299	S138 same (pin pad pads)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:30

EAST Search History

S14 0	8	up\$1down near (diode diodes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:31
S14 1	2055724	pin (external adj pin) pad (pad adj cell)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:32
S14 2	178158	S141 same (IC (internal adj circuit\$1) (integrated adj circuit\$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:32
S14 3	2308	S142 same (esd (electrostatic adj discharge))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:33
S14 4	803	S143 same (diode diodes)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:33
S14 5	337	S144 same (resistor buffer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:33
S14 6	272	S144 same (resistor (digital adj buffer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:47
S14 7	0	("2006/0050453").URPN.	USPAT	OR	OFF	2006/03/28 11:35
S14 8	0	("2006/0050453").URPN.	USPAT	OR	OFF	2006/03/28 11:35

EAST Search History

S14 9	0	S144 same ((digital adj buffer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 11:47
S15 0	145	S144 same (buffer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:07
S15 1	22567	esd (electrostatic adj discharge)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:08
S15 2	5193	S151 same (pin pad (external adj pin) (pad adj cell) (pads))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:08
S15 3	2428	S152 same (IC (internal adj circuit) (integrated adj circuit) (inner adj circuit))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:08
S15 5	512	S153 same (path paths (signal adj path))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:12
S15 6	33	S153 same ((signal adj path))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/28 12:12
S15 7	352889	(MOS transistor NMOS)	US-PGPUB; USPAT	OR	OFF	2006/03/28 14:44
S15 8	806	S157 same (gate near (control adj voltage))	US-PGPUB; USPAT	OR	OFF	2006/03/28 14:44
S15 9	6531	gate with (control adj voltage) with (control controls controlled controllable)	US-PGPUB; USPAT	OR	OFF	2006/03/28 14:45

EAST Search History

S16 0	2979	S159 with (MOS transistor)	US-PGPUB; USPAT	OR	OFF	2006/03/28 14:45
S16 1	78	S160 same (pin pad (external adj pin) (pad adj cell))	US-PGPUB; USPAT	OR	OFF	2006/03/28 14:46
S16 2	136	source with well with pin with (couple coupled connect\$4)	US-PGPUB; USPAT	OR	OFF	2006/03/28 16:08
S16 3	3	((("5602409") or ("5751525") or ("6236087")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/28 16:08
S16 4	766137	MOS transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:35
S16 5	40618	comparator same (MOS transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:35
S16 6	24354	S165 same input	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:36
S16 7	20900	S166 same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:36
S16 8	2030	S165 same (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:36
S16 9	1665	S168 same (second adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:37

EAST Search History

S17 0	212	S169 same (compare compared compares)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:40
S17 1	44898	"212" same (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:37
S17 2	6	S170 same (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/30 15:37
S17 3	225811	MOS mosfet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:26
S17 4	1192	S173 with gate with (control adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:27
S17 5	38	S174 same (pin pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:43
S17 6	342029	esd electrostatic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:43
S17 7	11663	S176 same (pad pin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:56

EAST Search History

S17 8	950	S177 same (MOS mosfet)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:43
S17 9	2396	S177 same (MOS mosfet transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 09:22
S18 0	603	S178 same (gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:43
S18 1	8	S180 same (control adj voltage)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:44
S18 2	15	("4859875" "5208719" "5237395").PN. OR ("6078487"). URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/03/31 08:54
S18 3	11663	S176 same (pad pin (pad adj cell) (external adj pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:57
S18 4	2396	S183 same (mos MOSFET transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:57
S18 5	114	S184 same (comparator compar\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 08:58
S18 6	12	S184 same (comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 09:00

EAST Search History

S18 7	125	S184 and (comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 09:00
S18 8	1576	(MOS mosfet transistor) near (comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:30
S18 9	66	S188 same (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 09:23
S19 0	42130	(MOS mosfet transistor) same (comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:30
S19 1	21701	S190 same input same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:30
S19 2	1816	S191 same (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:31
S19 3	1525	S192 same (second adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:31
S19 4	2099	S190 same (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:31

EAST Search History

S19 5	1725	S194 same (second adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:31
S19 6	1525	S195 same output	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:32
S19 7	793305	mos MOSFET transistor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:32
S19 8	90649	S197 and (pin pad (pad adj cell) (external adj pin))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:33
S19 9	15216	S198 and (comparator)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:33
S20 0	3469	S199 and (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:33
S20 1	3133	S200 and (second adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:33
S20 2	248	S201 and (esd electrostatic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:48

EAST Search History

S20 3	4138	(MOS mosfet) with (comparator (comparator adj circuit) (comarator adj circuitry))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:54
S20 4	108	S203 with (first adj input)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/31 10:54
S20 5	701	comparator same (SAR (SAR adj ADC) (flash adj ADC))	US-PGPUB; USPAT	OR	OFF	2006/04/01 14:07
S20 6	45	S205 same (MOS transistor mosfet)	US-PGPUB; USPAT	OR	OFF	2006/04/01 14:07
S20 7	810	comparator\$1 same (SAR (SAR adj ADC) (flash adj ADC))	US-PGPUB; USPAT	OR	OFF	2006/04/01 14:07
S20 8	52	S207 same (MOS transistor mosfet)	US-PGPUB; USPAT	OR	OFF	2006/04/01 14:07
S20 9	19	comparator with ((SAR adj ADC))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/04/03 07:22
S21 0	1	("6891490").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2006/04/03 07:22
S21 1	139	(signal adj paths) with (pad (pad adj cell))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:40
S21 2	23998	"bonding pads"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:40
S21 3	0	S212 and ((multi\$1signal or "two or more") near "bonding pad")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:42

EAST Search History

S21 4	0	S212 and ((multi\$1signal or "two or more") with "bonding pad")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:42
S21 5	0	S212 and ((multi\$1signal or "two or more") with ("bonding pad" or "pad cell"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:43
S21 6	0	S212 and ((multi\$1signal or "two or more") same ("bonding pad" or "pad cell"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:43
S21 7	20	S212 and (("signal paths" or "two or more") same ("bonding pad" or "pad cell"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/10/13 13:43